

FILM DEPOSITING APPARATUS AND FILM DEPOSITING METHOD

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Abstract

PROBLEM TO BE SOLVED: To provide a film depositing apparatus and a film depositing method in which an ALD method can be used with a high productivity without using any high-speed switching valve.

SOLUTION: The film depositing apparatus comprises a chamber 11 which houses a substrate W, a substrate support member 12 to support a plurality of substrate W in one plane in the chamber 11, a first treatment gas ejecting nozzle 20 which is provided in the chamber 11 and ejects $TiCl_4$, a second treatment gas ejecting nozzle 21 which ejects NH_3 , a rotary mechanism 14 to rotate the substrate support member 12, and a heater 16 to heat the substrate W, and a Ti monatomic layer and a N monatomic layer are alternately formed on the substrate W while rotating the substrate support member 12 to revolve the substrate W.